

# Wei D Lu

## List of Publications by Citations

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194  
papers

23,817  
citations

71  
h-index

154  
g-index

209  
ext. papers

27,250  
ext. citations

11  
avg, IF

7.47  
L-index

#	Paper	IF	Citations
194	Nanoscale memristor device as synapse in neuromorphic systems. <i>Nano Letters</i> , <b>2010</b> , 10, 1297-301	11.5	2772
193	Nanoelectronics from the bottom up. <i>Nature Materials</i> , <b>2007</b> , 6, 841-50	27	1290
192	Ge/Si nanowire heterostructures as high-performance field-effect transistors. <i>Nature</i> , <b>2006</b> , 441, 489-93	50.4	1262
191	Single-crystal metallic nanowires and metal/semiconductor nanowire heterostructures. <i>Nature</i> , <b>2004</b> , 430, 61-5	50.4	879
190	The future of electronics based on memristive systems. <i>Nature Electronics</i> , <b>2018</b> , 1, 22-29	28.4	813
189	Observation of conducting filament growth in nanoscale resistive memories. <i>Nature Communications</i> , <b>2012</b> , 3, 732	17.4	782
188	Semiconductor nanowires. <i>Journal Physics D: Applied Physics</i> , <b>2006</b> , 39, R387-R406	3	653
187	Short-term memory to long-term memory transition in a nanoscale memristor. <i>ACS Nano</i> , <b>2011</b> , 5, 7669-7676	16.7	645
186	A functional hybrid memristor crossbar-array/CMOS system for data storage and neuromorphic applications. <i>Nano Letters</i> , <b>2012</b> , 12, 389-95	11.5	639
185	Controlled deposition of individual single-walled carbon nanotubes on chemically functionalized templates. <i>Chemical Physics Letters</i> , <b>1999</b> , 303, 125-129	2.5	457
184	High-density crossbar arrays based on a Si memristive system. <i>Nano Letters</i> , <b>2009</b> , 9, 870-4	11.5	441
183	Electrochemical dynamics of nanoscale metallic inclusions in dielectrics. <i>Nature Communications</i> , <b>2014</b> , 5, 4232	17.4	411
182	One-dimensional hole gas in germanium/silicon nanowire heterostructures. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , <b>2005</b> , 102, 10046-51	11.5	401
181	Sparse coding with memristor networks. <i>Nature Nanotechnology</i> , <b>2017</b> , 12, 784-789	28.7	388
180	Synthesis and Fabrication of High-Performance n-Type Silicon Nanowire Transistors. <i>Advanced Materials</i> , <b>2004</b> , 16, 1890-1893	24	383
179	Experimental demonstration of a second-order memristor and its ability to biorealistically implement synaptic plasticity. <i>Nano Letters</i> , <b>2015</b> , 15, 2203-11	11.5	356
178	CMOS compatible nanoscale nonvolatile resistance switching memory. <i>Nano Letters</i> , <b>2008</b> , 8, 392-7	11.5	338

177	Mechanical properties of vapor-liquid-solid synthesized silicon nanowires. <i>Nano Letters</i> , <b>2009</b> , 9, 3934-9	11.5	316
176	Real-time detection of electron tunnelling in a quantum dot. <i>Nature</i> , <b>2003</b> , 423, 422-5	50.4	311
175	Comprehensive physical model of dynamic resistive switching in an oxide memristor. <i>ACS Nano</i> , <b>2014</b> , 8, 2369-76	16.7	301
174	Recommended Methods to Study Resistive Switching Devices. <i>Advanced Electronic Materials</i> , <b>2019</b> , 5, 1800143	6.4	297
173	A fully integrated reprogrammable memristor-CMOS system for efficient multiply-accumulate operations. <i>Nature Electronics</i> , <b>2019</b> , 2, 290-299	28.4	281
172	Reservoir computing using dynamic memristors for temporal information processing. <i>Nature Communications</i> , <b>2017</b> , 8, 2204	17.4	277
171	Stochastic memristive devices for computing and neuromorphic applications. <i>Nanoscale</i> , <b>2013</b> , 5, 5872-87	7.7	276
170	Synaptic behaviors and modeling of a metal oxide memristive device. <i>Applied Physics A: Materials Science and Processing</i> , <b>2011</b> , 102, 857-863	2.6	271
169	Biorealistic Implementation of Synaptic Functions with Oxide Memristors through Internal Ionic Dynamics. <i>Advanced Functional Materials</i> , <b>2015</b> , 25, 4290-4299	15.6	270
168	Ionic modulation and ionic coupling effects in MoS devices for neuromorphic computing. <i>Nature Materials</i> , <b>2019</b> , 18, 141-148	27	262
167	Fully transparent thin-film transistor devices based on SnO <sub>2</sub> nanowires. <i>Nano Letters</i> , <b>2007</b> , 7, 2463-9	11.5	260
166	Semiconductor nanowire devices. <i>Nano Today</i> , <b>2008</b> , 3, 12-22	17.9	252
165	Nanowire Transistor Performance Limits and Applications. <i>IEEE Transactions on Electron Devices</i> , <b>2008</b> , 55, 2859-2876	2.9	250
164	Programmable resistance switching in nanoscale two-terminal devices. <i>Nano Letters</i> , <b>2009</b> , 9, 496-500	11.5	235
163	Si/a-Si core/shell nanowires as nonvolatile crossbar switches. <i>Nano Letters</i> , <b>2008</b> , 8, 386-91	11.5	211
162	Nanoscale resistive switching devices: mechanisms and modeling. <i>Nanoscale</i> , <b>2013</b> , 5, 10076-92	7.7	197
161	Observation of conductance quantization in oxide-based resistive switching memory. <i>Advanced Materials</i> , <b>2012</b> , 24, 3941-6	24	190
160	Iodine Vacancy Redistribution in Organic-Inorganic Halide Perovskite Films and Resistive Switching Effects. <i>Advanced Materials</i> , <b>2017</b> , 29, 1700527	24	185

159	Controlled 3D buckling of silicon nanowires for stretchable electronics. <i>ACS Nano</i> , <b>2011</b> , 5, 672-8	16.7	176
158	High-performance transparent conducting oxide nanowires. <i>Nano Letters</i> , <b>2006</b> , 6, 2909-15	11.5	176
157	Complementary resistive switching in tantalum oxide-based resistive memory devices. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 203112	3.4	170
156	Oxide heterostructure resistive memory. <i>Nano Letters</i> , <b>2013</b> , 13, 2908-15	11.5	151
155	Crossbar RRAM Arrays: Selector Device Requirements During Read Operation. <i>IEEE Transactions on Electron Devices</i> , <b>2014</b> , 61, 1369-1376	2.9	149
154	Coherent single charge transport in molecular-scale silicon nanowires. <i>Nano Letters</i> , <b>2005</b> , 5, 1143-6	11.5	143
153	Optogenetics-Inspired Tunable Synaptic Functions in Memristors. <i>ACS Nano</i> , <b>2018</b> , 12, 1242-1249	16.7	142
152	Nanoscale resistive memory with intrinsic diode characteristics and long endurance. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 053106	3.4	134
151	An optoelectronic resistive switching memory with integrated demodulating and arithmetic functions. <i>Advanced Materials</i> , <b>2015</b> , 27, 2797-803	24	131
150	Resistance switching in polycrystalline BiFeO <sub>3</sub> thin films. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 042101	3.4	129
149	Experimental Demonstration of Feature Extraction and Dimensionality Reduction Using Memristor Networks. <i>Nano Letters</i> , <b>2017</b> , 17, 3113-3118	11.5	128
148	Temporal data classification and forecasting using a memristor-based reservoir computing system. <i>Nature Electronics</i> , <b>2019</b> , 2, 480-487	28.4	125
147	Transparent metallic Sb-doped SnO <sub>2</sub> nanowires. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 222107	3.4	122
146	MoS Memristors Exhibiting Variable Switching Characteristics toward Biorealistic Synaptic Emulation. <i>ACS Nano</i> , <b>2018</b> , 12, 9240-9252	16.7	119
145	On-Demand Reconfiguration of Nanomaterials: When Electronics Meets Ionics. <i>Advanced Materials</i> , <b>2018</b> , 30, 1702770	24	116
144	Crossbar RRAM Arrays: Selector Device Requirements During Write Operation. <i>IEEE Transactions on Electron Devices</i> , <b>2014</b> , 61, 2820-2826	2.9	116
143	A general memristor-based partial differential equation solver. <i>Nature Electronics</i> , <b>2018</b> , 1, 411-420	28.4	112
142	Memristive Physically Evolving Networks Enabling the Emulation of Heterosynaptic Plasticity. <i>Advanced Materials</i> , <b>2015</b> , 27, 7720-7	24	110

141	Nanostructured thin films made by dewetting method of layer-by-layer assembly. <i>Nano Letters</i> , <b>2007</b> , 7, 3266-73	11.5	110
140	Tuning Ionic Transport in Memristive Devices by Graphene with Engineered Nanopores. <i>ACS Nano</i> , <b>2016</b> , 10, 3571-9	16.7	106
139	MoS2 transistors fabricated via plasma-assisted nanoprinting of few-layer MoS2 flakes into large-area arrays. <i>ACS Nano</i> , <b>2013</b> , 7, 5870-81	16.7	104
138	Nanoscale electrochemistry using dielectric thin films as solid electrolytes. <i>Nanoscale</i> , <b>2016</b> , 8, 13828-37	7.7	102
137	Random telegraph noise and resistance switching analysis of oxide based resistive memory. <i>Nanoscale</i> , <b>2014</b> , 6, 400-4	7.7	97
136	Electrochemical metallization cells blending nanoionics into nanoelectronics?. <i>MRS Bulletin</i> , <b>2012</b> , 37, 124-130	3.2	96
135	Doping-dependent electrical characteristics of SnO2 nanowires. <i>Small</i> , <b>2008</b> , 4, 451-4	11	93
134	Transparent, high-performance thin-film transistors with an InGaZnO/aligned-SnO2 -nanowire composite and their application in photodetectors. <i>Advanced Materials</i> , <b>2014</b> , 26, 7399-404	24	91
133	Branched SnO2 nanowires on metallic nanowire backbones for ethanol sensors application. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 102101	3.4	90
132	Tuning resistive switching characteristics of tantalum oxide memristors through Si doping. <i>ACS Nano</i> , <b>2014</b> , 8, 10262-9	16.7	85
131	A resistance-switchable and ferroelectric metal-organic framework. <i>Journal of the American Chemical Society</i> , <b>2014</b> , 136, 17477-83	16.4	85
130	Very Low-Programming-Current RRAM With Self-Rectifying Characteristics. <i>IEEE Electron Device Letters</i> , <b>2016</b> , 37, 404-407	4.4	80
129	Power-efficient combinatorial optimization using intrinsic noise in memristor Hopfield neural networks. <i>Nature Electronics</i> , <b>2020</b> , 3, 409-418	28.4	79
128	Strong and tunable spin-orbit coupling of one-dimensional holes in Ge/Si core/shell nanowires. <i>Nano Letters</i> , <b>2010</b> , 10, 2956-60	11.5	79
127	Building Neuromorphic Circuits with Memristive Devices. <i>IEEE Circuits and Systems Magazine</i> , <b>2013</b> , 13, 56-73	3.2	76
126	Data Clustering using Memristor Networks. <i>Scientific Reports</i> , <b>2015</b> , 5, 10492	4.9	75
125	Device and SPICE modeling of RRAM devices. <i>Nanoscale</i> , <b>2011</b> , 3, 3833-40	7.7	72
124	Ambipolar inverters using SnO thin-film transistors with balanced electron and hole mobilities. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 263502	3.4	72

123	K-means Data Clustering with Memristor Networks. <i>Nano Letters</i> , <b>2018</b> , 18, 4447-4453	11.5	68
122	Two-terminal resistive switches (memristors) for memory and logic applications <b>2011</b> ,		68
121	Utilizing multiple state variables to improve the dynamic range of analog switching in a memristor. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 173105	3.4	67
120	A Native Stochastic Computing Architecture Enabled by Memristors. <i>IEEE Nanotechnology Magazine</i> , <b>2014</b> , 13, 283-293	2.6	67
119	Oxide resistive memory with functionalized graphene as built-in selector element. <i>Advanced Materials</i> , <b>2014</b> , 26, 3693-9	24	61
118	Emulation of synaptic metaplasticity in memristors. <i>Nanoscale</i> , <b>2017</b> , 9, 45-51	7.7	56
117	Real-Time Observation of the Electrode-Size-Dependent Evolution Dynamics of the Conducting Filaments in a SiO Layer. <i>ACS Nano</i> , <b>2017</b> , 11, 4097-4104	16.7	55
116	Feature Extraction Using Memristor Networks. <i>IEEE Transactions on Neural Networks and Learning Systems</i> , <b>2016</b> , 27, 2327-2336	10.3	54
115	Nanoscale resistive switching devices for memory and computing applications. <i>Nano Research</i> , <b>2020</b> , 13, 1228-1243	10	53
114	ITO nanowires and nanoparticles for transparent films. <i>MRS Bulletin</i> , <b>2011</b> , 36, 782-788	3.2	53
113	Efficient in-memory computing architecture based on crossbar arrays <b>2015</b> ,		51
112	Memristor networks for real-time neural activity analysis. <i>Nature Communications</i> , <b>2020</b> , 11, 2439	17.4	50
111	Parasitic Effect Analysis in Memristor-Array-Based Neuromorphic Systems. <i>IEEE Nanotechnology Magazine</i> , <b>2018</b> , 17, 184-193	2.6	46
110	In Situ Nanoscale Electric Field Control of Magnetism by Nanoionics. <i>Advanced Materials</i> , <b>2016</b> , 28, 7658-65	14	44
109	Multifunctional Nanoionic Devices Enabling Simultaneous Heterosynaptic Plasticity and Efficient In-Memory Boolean Logic. <i>Advanced Electronic Materials</i> , <b>2017</b> , 3, 1700032	6.4	43
108	Filament-Free Bulk Resistive Memory Enables Deterministic Analogue Switching. <i>Advanced Materials</i> , <b>2020</b> , 32, e2003984	24	43
107	Charge Transition of Oxygen Vacancies during Resistive Switching in Oxide-Based RRAM. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 11579-11586	9.5	42
106	Conduction mechanism of a TaO(x)-based selector and its application in crossbar memory arrays. <i>Nanoscale</i> , <b>2015</b> , 7, 4964-70	7.7	38

105	Nanoimprint-Assisted Shear Exfoliation (NASE) for Producing Multilayer MoS <sub>2</sub> Structures as Field-Effect Transistor Channel Arrays. <i>ACS Nano</i> , <b>2015</b> , 9, 8773-85	16.7	36
104	Single-Readout High-Density Memristor Crossbar. <i>Scientific Reports</i> , <b>2016</b> , 6, 18863	4.9	36
103	Electronic and optical properties of oxygen vacancies in amorphous TaO from first principles. <i>Nanoscale</i> , <b>2017</b> , 9, 1120-1127	7.7	34
102	Vertical Ge/Si Core/Shell Nanowire Junctionless Transistor. <i>Nano Letters</i> , <b>2016</b> , 16, 420-6	11.5	33
101	Retention failure analysis of metal-oxide based resistive memory. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 1135-10	5.10	33
100	Memristive devices for stochastic computing <b>2014</b> ,		32
99	Abnormal Multiple Charge Memory States in Exfoliated Few-Layer WSe Transistors. <i>ACS Nano</i> , <b>2017</b> , 11, 1091-1102	16.7	30
98	Ge nanowire photodetector with high photoconductive gain epitaxially integrated on Si substrate. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 173104	3.4	30
97	Vertical nanowire heterojunction devices based on a clean Si/Ge interface. <i>Nano Letters</i> , <b>2013</b> , 13, 5521-7	11.5	30
96	Memristive computing devices and applications. <i>Journal of Electroceramics</i> , <b>2017</b> , 39, 4-20	1.5	30
95	. <i>IEEE Electron Device Letters</i> , <b>2014</b> , 35, 1239-1241	4.4	30
94	Esaki tunnel diodes based on vertical Si-Ge nanowire heterojunctions. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 092108	3.4	29
93	Nanoionic Resistive-Switching Devices. <i>Advanced Electronic Materials</i> , <b>2019</b> , 5, 1900184	6.4	27
92	Neuromorphic Computing Using Memristor Crossbar Networks: A Focus on Bio-Inspired Approaches. <i>IEEE Nanotechnology Magazine</i> , <b>2018</b> , 12, 6-18	1.7	27
91	A Deep Neural Network Accelerator Based on Tiled RRAM Architecture <b>2019</b> ,		27
90	Metal/Ion Interactions Induced p-i-n Junction in Methylammonium Lead Triiodide Perovskite Single Crystals. <i>Journal of the American Chemical Society</i> , <b>2017</b> , 139, 17285-17288	16.4	25
89	Progress in the Characterizations and Understanding of Conducting Filaments in Resistive Switching Devices. <i>IEEE Nanotechnology Magazine</i> , <b>2016</b> , 15, 465-472	2.6	25
88	Temporal Learning Using Second-Order Memristors. <i>IEEE Nanotechnology Magazine</i> , <b>2017</b> , 16, 721-723	2.6	24

87	Field-Programmable Crossbar Array (FPCA) for Reconfigurable Computing. <i>IEEE Transactions on Multi-Scale Computing Systems</i> , <b>2018</b> , 4, 698-710		24
86	Self-Assembly for Semiconductor Industry. <i>IEEE Transactions on Semiconductor Manufacturing</i> , <b>2007</b> , 20, 421-431	2.6	24
85	Memristive technologies for data storage, computation, encryption, and radio-frequency communication. <i>Science</i> , <b>2022</b> , 376,	33.3	24
84	Electronic properties of tantalum pentoxide polymorphs from first-principles calculations. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 202108	3.4	23
83	Room temperature magnetic exchange coupling in multiferroic BaTiO <sub>3</sub> /CoFe <sub>2</sub> O <sub>4</sub> magnetoelectric superlattice. <i>Journal of Materials Science</i> , <b>2009</b> , 44, 5143-5148	4.3	22
82	Spatial confinement of carriers and tunable band structures in InAs/InP-core-shell nanowires. <i>Chemical Physics Letters</i> , <b>2010</b> , 495, 261-265	2.5	22
81	X-ray diffraction and Raman scattering study of SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> ceramics and thin films with Bi <sub>3</sub> TiNbO <sub>9</sub> addition. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 3827-3829	3.4	22
80	Si Memristive devices applied to memory and neuromorphic circuits <b>2010</b> ,		21
79	Near infrared neuromorphic computing via upconversion-mediated optogenetics. <i>Nano Energy</i> , <b>2020</b> , 67, 104262	17.1	21
78	Adaptive Synaptic Memory via Lithium Ion Modulation in RRAM Devices. <i>Small</i> , <b>2020</b> , 16, e2003964	11	21
77	Pattern recognition with memristor networks <b>2014</b> ,		20
76	Latch-up based bidirectional npn selector for bipolar resistance-change memory. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 033505	3.4	19
75	Radio frequency nanowire resonators and in situ frequency tuning. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 203104	3.4	18
74	Single-electron transistor strongly coupled to an electrostatically defined quantum dot. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 2746-2748	3.4	18
73	Neuromorphic computing with memristive devices. <i>Science China Information Sciences</i> , <b>2018</b> , 61, 1	3.4	18
72	Quantitative, Dynamic TaOx Memristor/Resistive Random Access Memory Model. <i>ACS Applied Electronic Materials</i> , <b>2020</b> , 2, 701-709	4	17
71	In Situ Nano-thermomechanical Experiment Reveals Brittle to Ductile Transition in Silicon Nanowires. <i>Nano Letters</i> , <b>2019</b> , 19, 5327-5334	11.5	17
70	Hardware Acceleration of Simulated Annealing of Spin Glass by RRAM Crossbar Array <b>2018</b> ,		16



69	Interference and memory capacity effects in memristive systems. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 083106	10.6	15
68	Radio-Frequency Operation of Transparent Nanowire Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , <b>2009</b> , 30, 730-732	4.4	15
67	Dynamical memristors for higher-complexity neuromorphic computing. <i>Nature Reviews Materials</i> ,	73.3	15
66	FPAA/Memristor Hybrid Computing Infrastructure. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , <b>2015</b> , 62, 906-915	3.9	14
65	Self-Limited and Forming-Free CBRAM Device With Double Al <sub>2</sub> O <sub>3</sub> ALD Layers. <i>IEEE Electron Device Letters</i> , <b>2018</b> , 39, 1512-1515	4.4	14
64	Time-dependency of the threshold voltage in memristive devices <b>2011</b> ,		13
63	A Fully Integrated Reprogrammable CMOS-RRAM Compute-in-Memory Coprocessor for Neuromorphic Applications. <i>IEEE Journal on Exploratory Solid-State Computational Devices and Circuits</i> , <b>2020</b> , 1-1	2.4	12
62	Chapter 1:Semiconductor Nanowire Growth and Integration. <i>RSC Smart Materials</i> , <b>2014</b> , 1-53	0.6	12
61	Growth and electrical properties of Al-catalyzed Si nanowires. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 033108	3.4	12
60	Temporal information encoding in dynamic memristive devices. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 193103	3.4	11
59	Charge transport processes in a superconducting single-electron transistor coupled to a microstrip transmission line. <i>Physical Review B</i> , <b>2002</b> , 65,	3.3	11
58	Memristive Stochastic Computing for Deep Learning Parameter Optimization. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , <b>2021</b> , 68, 1650-1654	3.5	11
57	Scaling behavior of nanoimprint and nanoprinting lithography for producing nanostructures of molybdenum disulfide. <i>Microsystems and Nanoengineering</i> , <b>2017</b> , 3, 17053	7.7	10
56	A Low-Power Variation-Aware Adaptive Write Scheme for Access-Transistor-Free Memristive Memory. <i>ACM Journal on Emerging Technologies in Computing Systems</i> , <b>2015</b> , 12, 1-18	1.7	10
55	How to Build a Memristive Integrate-and-Fire Model for Spiking Neuronal Signal Generation. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , <b>2021</b> , 68, 4837-4850	3.9	9
54	Memristors Based on (Zr, Hf, Nb, Ta, Mo, W) High-Entropy Oxides. <i>Advanced Electronic Materials</i> , <b>2021</b> , 7, 2001258	6.4	9
53	Device nonideality effects on image reconstruction using memristor arrays <b>2016</b> ,		9
52	Efficient Si Nanowire Array Transfer via Bi-Layer Structure Formation Through Metal-Assisted Chemical Etching. <i>Advanced Functional Materials</i> , <b>2014</b> , 24, 1949-1955	15.6	8

51	Modeling and implementation of oxide memristors for neuromorphic applications <b>2012,</b>		8
50	A high-speed MIM resistive memory cell with an inherent vanadium selector. <i>Applied Materials Today</i> , <b>2020</b> , 21, 100848	6.6	7
49	A Crossbar-Based In-Memory Computing Architecture. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , <b>2020</b> , 67, 4224-4232	3.9	7
48	Andreev tunneling enhanced by Coulomb oscillations in superconductor-semiconductor hybrid Ge/Si nanowire devices. <i>Physical Review B</i> , <b>2011</b> , 84,	3.3	7
47	Organic vapor discrimination with chemiresistor arrays of temperature modulated tin-oxide nanowires and thiolate-monolayer-protected gold nanoparticles. <i>Nanotechnology</i> , <b>2011</b> , 22, 125501	3.4	7
46	Stabilization of Mode-Dependent Impulsive Hybrid Systems Driven by DFA With Mixed-Mode Effects. <i>IEEE Transactions on Neural Networks and Learning Systems</i> , <b>2020</b> , 31, 1616-1625	10.3	7
45	Memristors and Memristive Devices for Neuromorphic Computing <b>2014</b> , 129-149		6
44	3-D Vertical Dual-Layer Oxide Memristive Devices. <i>IEEE Transactions on Electron Devices</i> , <b>2014</b> , 61, 2581-2583		5
43	Superconducting single-electron transistor coupled to a locally tunable electromagnetic environment. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 4976-4978	3.4	5
42	Memristor-Based Binarized Spiking Neural Networks: Challenges and Applications.. <i>IEEE Nanotechnology Magazine</i> , <b>2022</b> , 2-11	1.7	5
41	Memristive Devices: Switching Effects, Modeling, and Applications <b>2014</b> , 195-221		4
40	Memristive analog arithmetic within cellular arrays <b>2012,</b>		3
39	Device Variation Effects on Neural Network Inference Accuracy in Analog In-Memory Computing Systems. <i>Advanced Intelligent Systems</i> , 2100199	6	3
38	RRAM Solutions for Stochastic Computing <b>2019</b> , 153-164		3
37	RRAM fabric for neuromorphic and reconfigurable compute-in-memory systems <b>2018,</b>		3
36	Defect considerations for robust sparse coding using memristor arrays <b>2015,</b>		2
35	A Real-Time Retinomorphic Simulator Using a Conductance-Based Discrete Neuronal Network <b>2020</b> ,		2
34	Epsilon-greedy strategy for online dictionary learning with realistic memristor array constraints <b>2017,</b>		2

33	Analog signal processing on a FPAA/memristor hybrid circuit <b>2014</b> ,		2
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